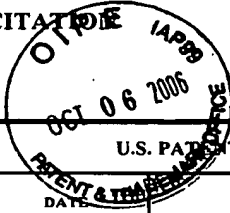


INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				Docket Number (Optional) F05-420-US		Application Number 10/564,416	
				Applicant(s) Masanobu ANDO, et al.			
				Filing Date January 12, 2006		Group Art Unit 2811	



U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

U.S. PATENT APPLICATION PUBLICATIONS

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FOREIGN PATENT DOCUMENTS

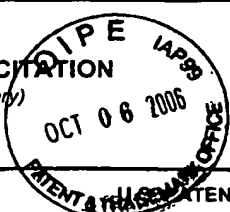
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
	EP-0 662 739	07/12/1995	Europe	Previously submitted with IDS dated 4/12/06			
	11-026812	01/29/1999	Japan	Previously submitted with IDS dated 4/12/06			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		European Search Report dated June 2, 2006
		Kneissl, Michael, et al., "Continuous-wave ultraviolet InGaN/InAlGaN multiple quantum well laser diodes", Applied Physics Letters, AIP, American Institute of Physics, Melville, NY, US, Vol. 82, No. 15, April 14, 2003, Pages 2386-2388, 012033738 Previously submitted with IDS dated 4/12/06

EXAMINER /Sara Crane/	DATE CONSIDERED 12/23/2006
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				ATTY DOCKET NO.		APPLICATION NO.		
		F05-420-US		10/564.416				
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FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
		Nakamura, et al., "InGaN/GaN/AlGaIn based laser diodes with modulation-doped strained-layer superlattices grown on an epitaxially laterally overgrown GaN substrate", Applied Physics Letter, AIP, American Institute of Physics, Melville, NY, US, Vol. 72, No. 2, January 12, 1998 previously submitted with IDS dated 4/12/06						
EXAMINER /Sara Crane/				DATE CONSIDERED 12/23/2006				
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